

SEMICONDUCTOR PRODUCT							
2 S C 2 0 5 0				C.B.C			
TYPE	GPN Epitaxial Planar						
MATERIAL	Silicon						
APPLICATION	High Frequency Power Amplifier for 270MHz Band AM/SSB Transceiver						
OUTLINE	See Fig 1						
CONNECTION	See Fig 1						
ABSOLUTE MAXIMUM RATINGS	V _{CEO} (V)	V _{CEB} ^{*1} (V)	V _{BEBO} (V)	I _C ^{*2} (A)	P ₀ (W)	T _j (°C)	°ctg (°C)
	70	70	4.0	8	25	150	-55 ~ +150
Ta = 25°C							
TEST SPECIFICATION Ta = 25°C							
Symbol	Condition	Typ.	Limit		Unit		
			Min	Max			
I _{CBO}	V _{CB} =40V, I _E =0			20	μA		
h _{FE}	V _{CE} =10V, I _C =2.0A		20	150			
V _{CE(sat)}	I _C =2.0A, I _B =0.4A	0.2		0.5	V		
f _T	V _{CE} =10V, I _C =0.5A	150			MHz		
C _{ob}	V _{CB} =10V, f=1MHz, I _E =0	80			PF		
P ₀	V _{CC} =12V, f=50MHz, P _i =3W		13.0		W		
η _c	V _{CC} =12V, f=50MHz, P _i =3W		60		%		
<p>*1 R_{BE}=100Ω</p> <p>*2 P_W=20mS, Duty Cycle 50%</p> <p style="text-align: right;">Fig 1</p>							
51.1.25				MITSUBISHI ELECTRONICS CORPORATION SEMICONDUCTOR DIVISION			



3 C 2 0 5 0 (TOP66)

